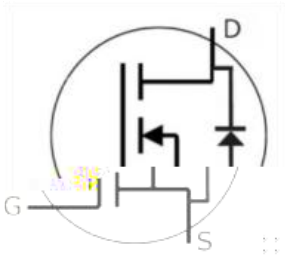
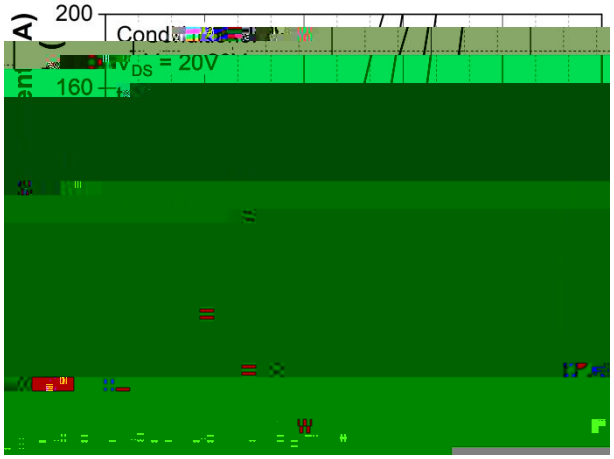
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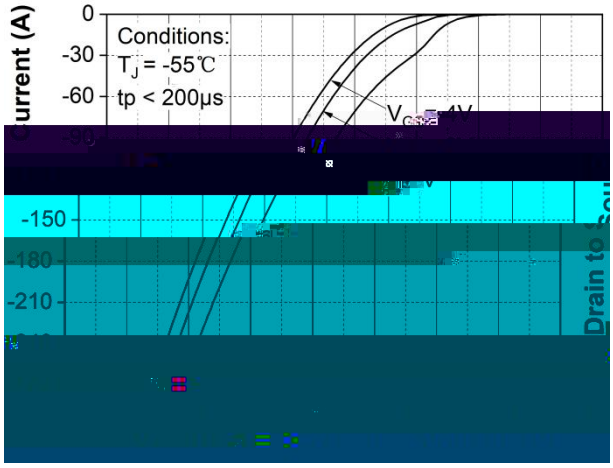

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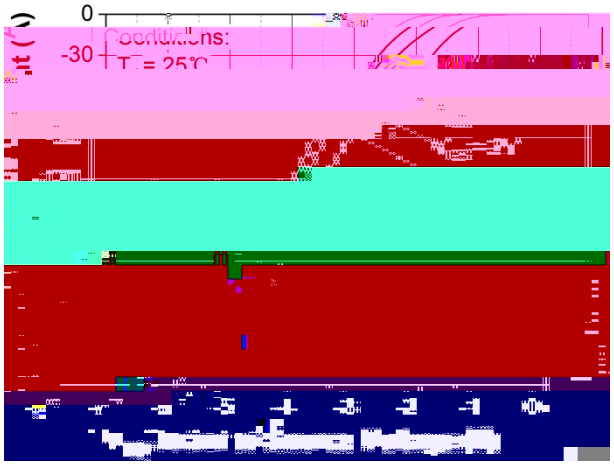
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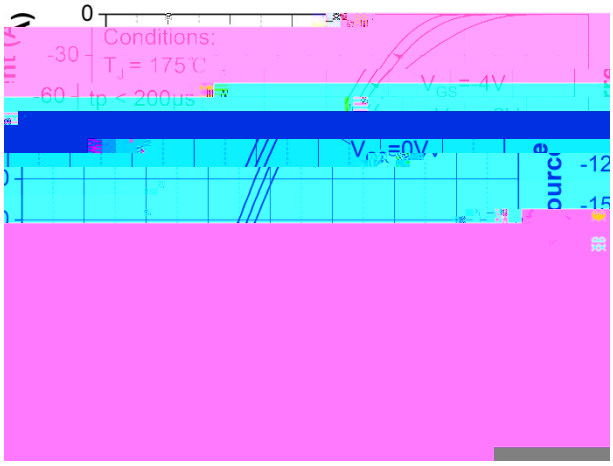
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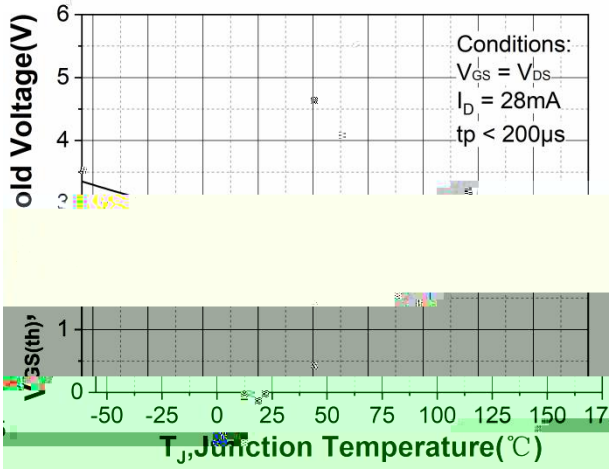
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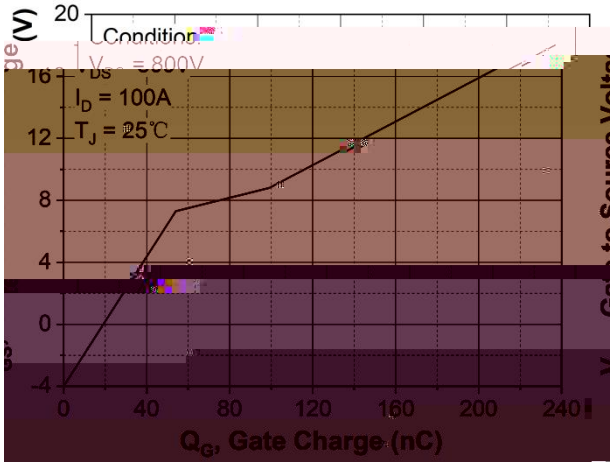

200
160
V_{DS} = 20V


0
-30
-60
-150
-180
-210
Conditions:
T_J = -55℃
tp < 200μs
V_{GS}=-4V
Drain to

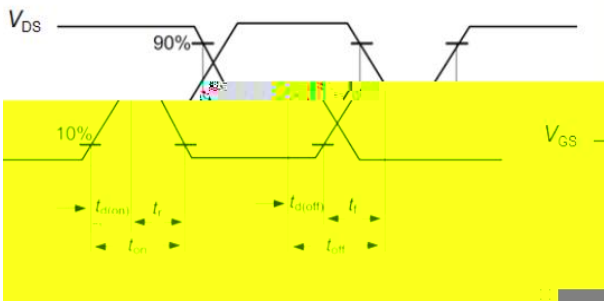

0
-30
Conditions:

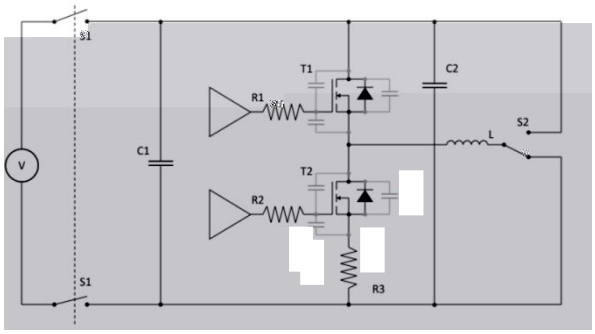

0
-30
-60
Conditions:
T_J = 175℃
tp < 200μs
V_{GS}=-4V
V_{GS}=0V
-12
-15

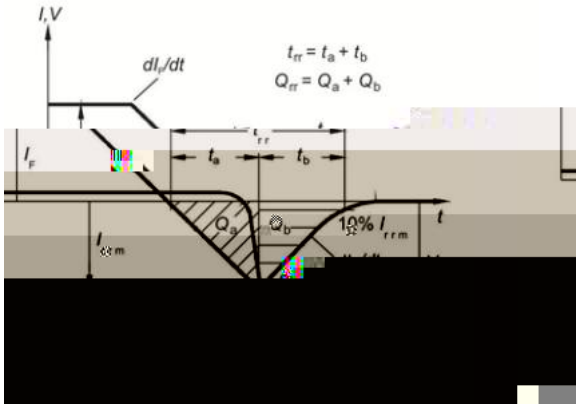

6
5
4
1
0
Conditions:
V_{GS} = V_{DS}
I_D = 28mA
tp < 200μs
-50 -25 0 25 50 75 100 125 150 17
T_J,Junction Temperature(℃)


20
16
12
8
4
0
-4
Condition
V_{DS} = 800V
I_D = 100A
T_J = 25℃
0 40 80 120 160 200 240
Q_G, Gate Charge (nC)




V_{DS}
90%
10%
V_{GS}
$t_{d(on)}$
t_r
t_{on}
$t_{d(off)}$
t_f
t_{off}


S1
T1
C2
R1
S2
L
V
C1
T2
R2
S1
R3


I,V
dI_F/dt
$t_{rr} = t_a + t_b$
$Q_{rr} = Q_a + Q_b$
t_{rr}
I_F
t_a
t_b
Q_a
Q_b
10% I_{rrm}
t
I_{rrm}

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		——	——
			——

I X D LWWH •0I L

WK